

MOS FIELD EFFECT TRANSISTOR

2SK2410

SWITCHING N-CHANNEL POWER MOS FET INDUSTRIAL USE

DESCRIPTION

The 2SK2410 is N-Channel MOS Field Effect Transistor designed for high speed switching applications.

FEATURES

- Low On-Resistance
 $R_{DS(on)1} = 40 \text{ m}\Omega \text{ MAX. (@ } V_{GS} = 10 \text{ V, } I_D = 15 \text{ A)}$
 $R_{DS(on)2} = 60 \text{ m}\Omega \text{ MAX. (@ } V_{GS} = 4 \text{ V, } I_D = 15 \text{ A)}$
- Low C_{iss} $C_{iss} = 1500 \text{ pF TYP.}$
- High Avalanche Capability Ratings
- Built-in G-S Gate Protection Diodes

QUALITY GRADE

Standard

Please refer to "Quality grade on NEC Semiconductor Devices" (Document number IEI-1209) published by NEC Corporation to know the specification of quality grade on the devices and its recommended applications.

ABSOLUTE MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$)

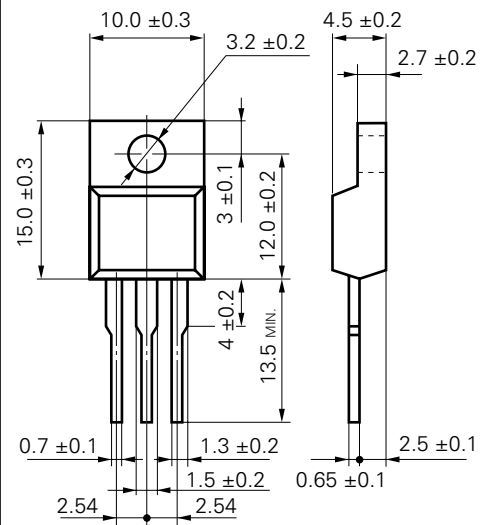
Drain to Source Voltage	V_{DSS}	60	V
Gate to Source Voltage	V_{GSS}	± 20	V
Drain Current (DC)	$I_{D(DC)}$	± 30	A
Drain Current (pulse)*	$I_{D(pulse)}$	± 120	A
Total Power Dissipation ($T_c = 25^\circ\text{C}$)	P_{T1}	35	W
Total Power Dissipation ($T_A = 25^\circ\text{C}$)	P_{T2}	2.0	W
Channel Temperature	T_{ch}	150	$^\circ\text{C}$
Storage Temperature	T_{stg}	-55 to +150	$^\circ\text{C}$
Single Avalanche Current**	I_{AS}	30	A
Single Avalanche Energy**	E_{AS}	90	mJ

* $PW \leq 10 \mu\text{s}$, Duty Cycle $\leq 1\%$

** Starting $T_{ch} = 25^\circ\text{C}$, $R_G = 25 \Omega$, $V_{GS} = 20 \text{ V} \rightarrow 0$

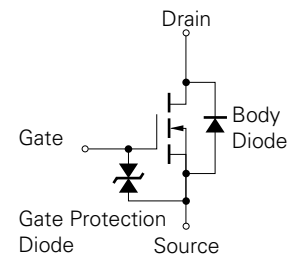
PACKAGE DIMENSIONS

(in millimeters)



1. Gate
2. Drain
3. Source

MP-45F (ISOLATED TO-220)

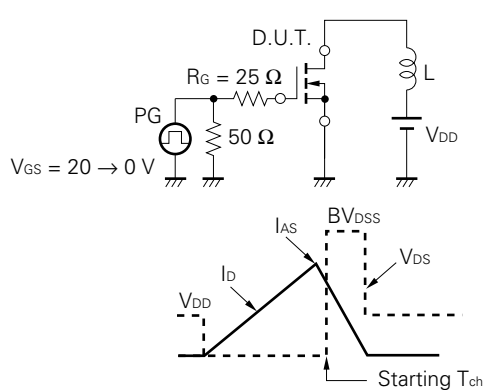


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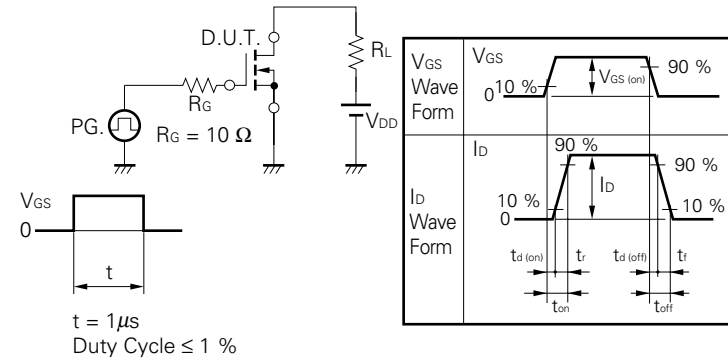
ELECTRICAL CHARACTERISTICS ($T_A = 25\text{ }^{\circ}\text{C}$)

CHARACTERISTIC	SYMBOL	MIN.	TYP.	MAX.	UNIT	TEST CONDITIONS
Drain to Source On-Resistance	$R_{DS(on)1}$		31	40	$\text{m}\Omega$	$V_{GS} = 10\text{ V}$, $I_D = 15\text{ A}$
Drain to Source On-Resistance	$R_{DS(on)2}$		40	60	$\text{m}\Omega$	$V_{GS} = 4\text{ V}$, $I_D = 15\text{ A}$
Gate to Source Cutoff Voltage	$V_{GS(off)}$	1.0	1.5	2.0	V	$V_{DS} = 10\text{ V}$, $I_D = 1\text{ mA}$
Forward Transfer Admittance	$ y_{fs} $	15	27		S	$V_{DS} = 10\text{ V}$, $I_D = 15\text{ A}$
Drain Leakage Current	I_{bss}			10	μA	$V_{DS} = 60\text{ V}$, $V_{GS} = 0$
Gate to Source Leakage Current	I_{GSS}			± 10	μA	$V_{GS} = \pm 20\text{ V}$, $V_{DS} = 0$
Input Capacitance	C_{iss}		1500		pF	$V_{DS} = 10\text{ V}$
Output Capacitance	C_{oss}		720		pF	$V_{GS} = 0$
Reverse Transfer Capacitance	C_{rss}		190		pF	$f = 1\text{ MHz}$
Turn-On Delay Time	$t_{d(on)}$		22		ns	$I_D = 15\text{ A}$
Rise Time	t_r		260		ns	$V_{GS(on)} = 10\text{ V}$
Turn-Off Delay Time	$t_{d(off)}$		130		ns	$V_{DD} = 30\text{ V}$
Fall Time	t_f		150		ns	$R_G = 10\text{ }\Omega$
Total Gate Charge	Q_G		50		nC	$I_D = 30\text{ A}$
Gate to Source Charge	Q_{GS}		5.0		nC	$V_{DD} = 48\text{ V}$
Gate to Drain Charge	Q_{GD}		15		nC	$V_{GS} = 10\text{ V}$
Body Diode Forward Voltage	$V_{F(S-D)}$		1.1		V	$I_F = 30\text{ A}$, $V_{GS} = 0$
Reverse Recovery Time	t_{rr}		110		ns	$I_F = 30\text{ A}$, $V_{GS} = 0$
Reverse Recovery Charge	Q_{rr}		320		nC	$di/dt = 100\text{ A}/\mu\text{s}$

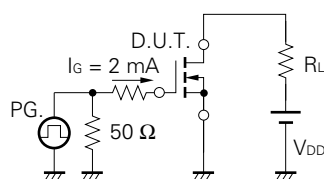
Test Circuit 1 Avalanche Capability



Test Circuit 2 Switching Time

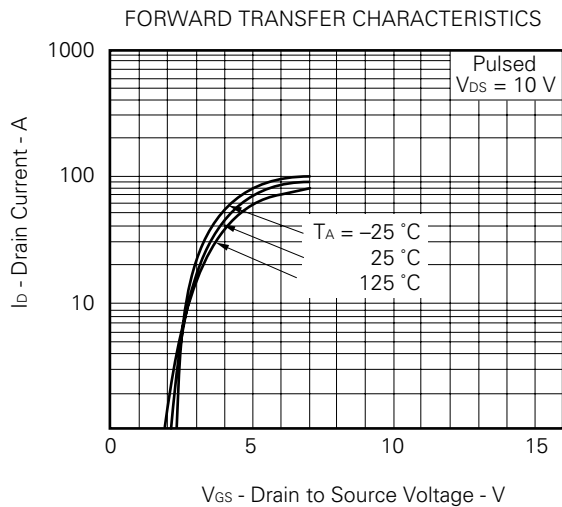
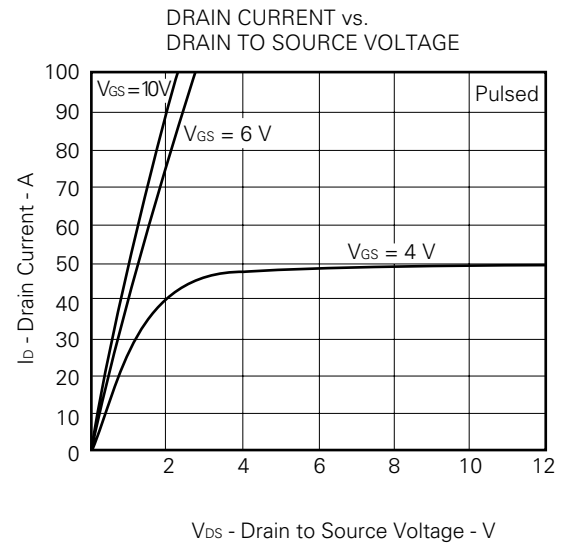
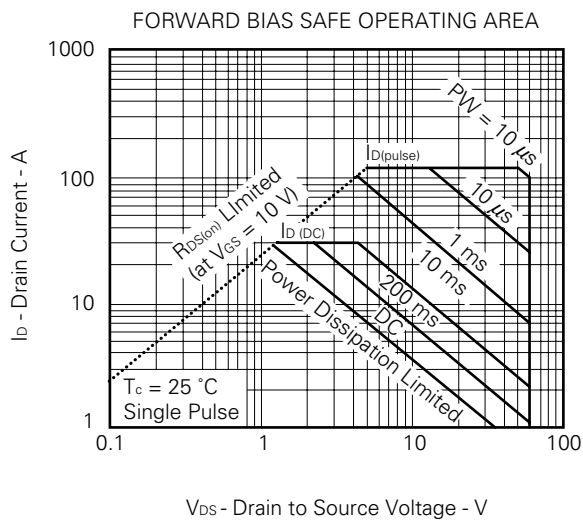
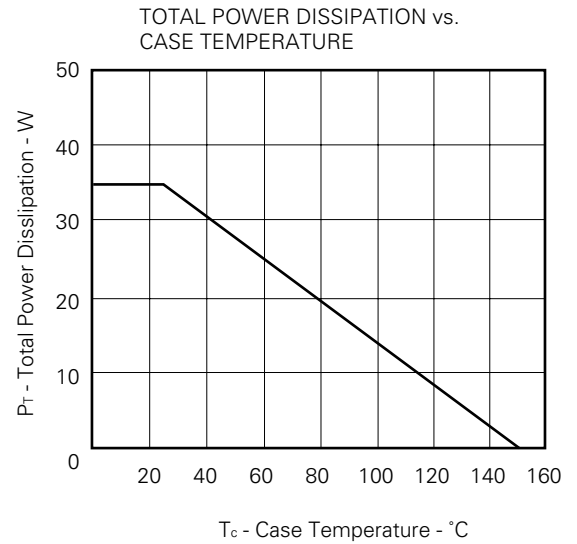
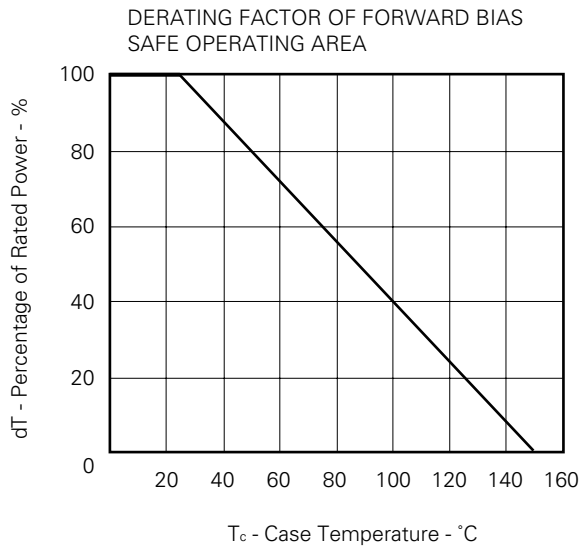


Test Circuit 3 Gate Charge

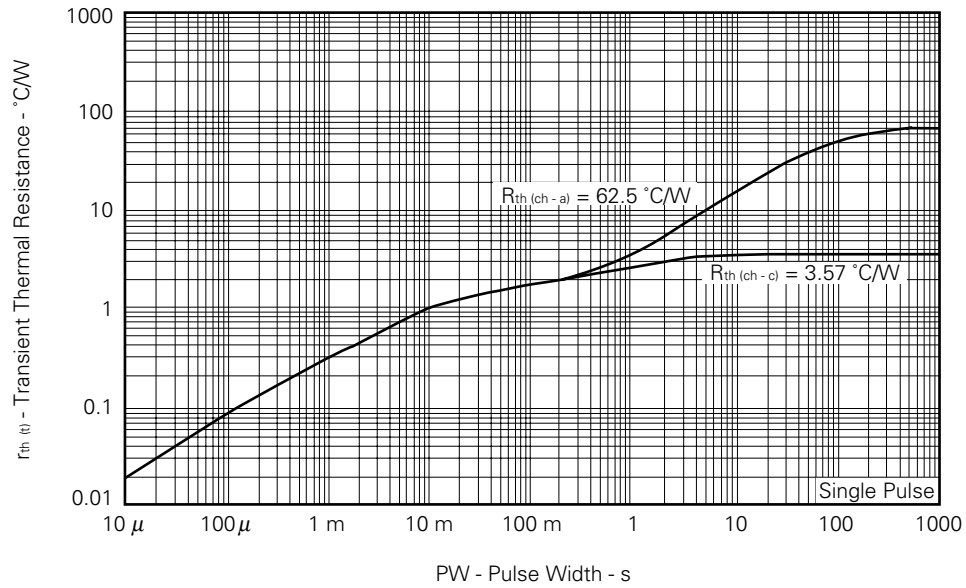


The application circuits and their parameters are for references only and are not intended for use in actual design-in's.

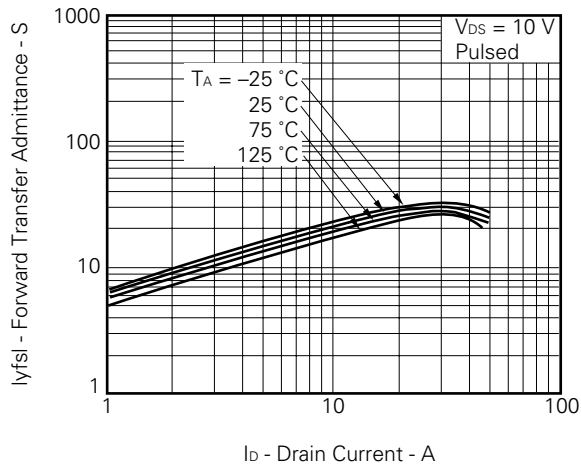
TYPICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$)



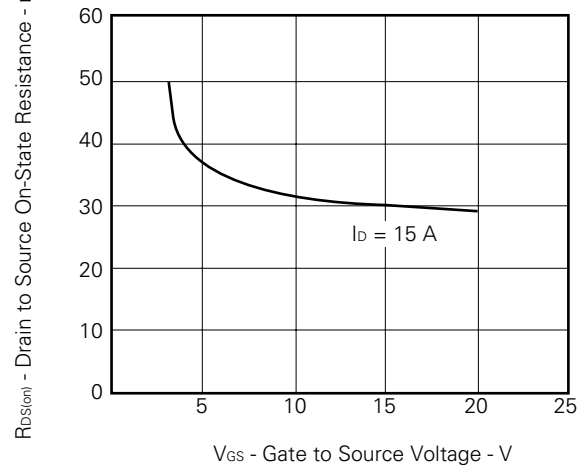
TRANSIENT THERMAL RESISTANCE vs. PULSE WIDTH



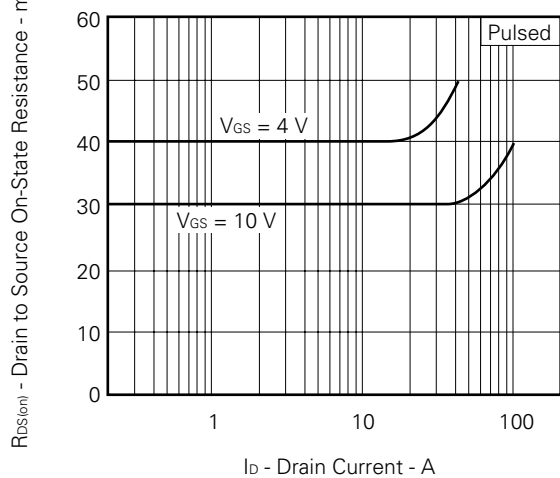
FORWARD TRANSFER ADMITTANCE vs. DRAIN CURRENT



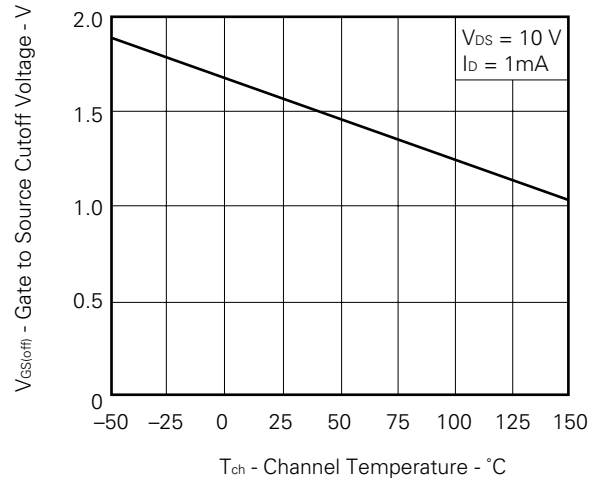
DRAIN TO SOURCE ON-STATE RESISTANCE vs. GATE TO SOURCE VOLTAGE

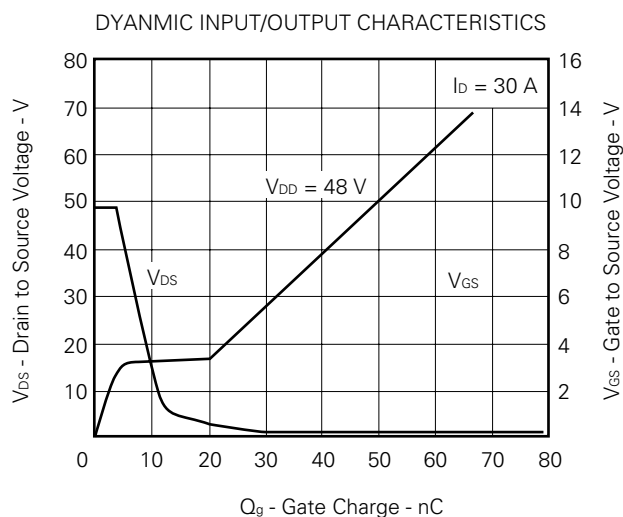
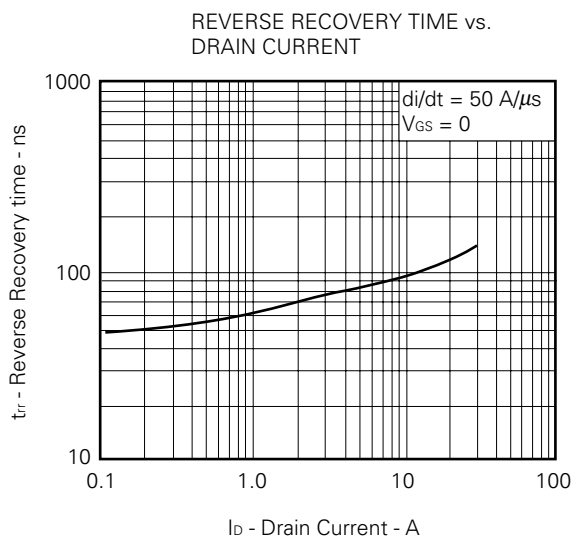
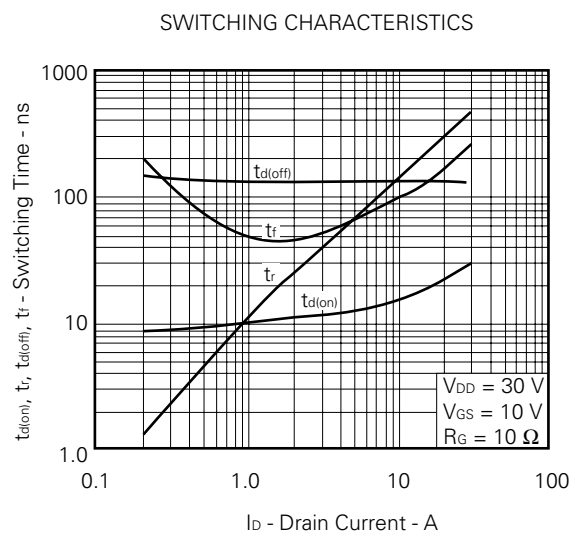
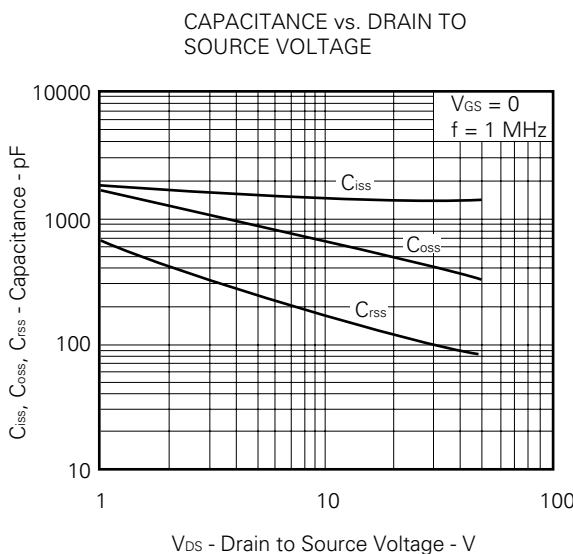
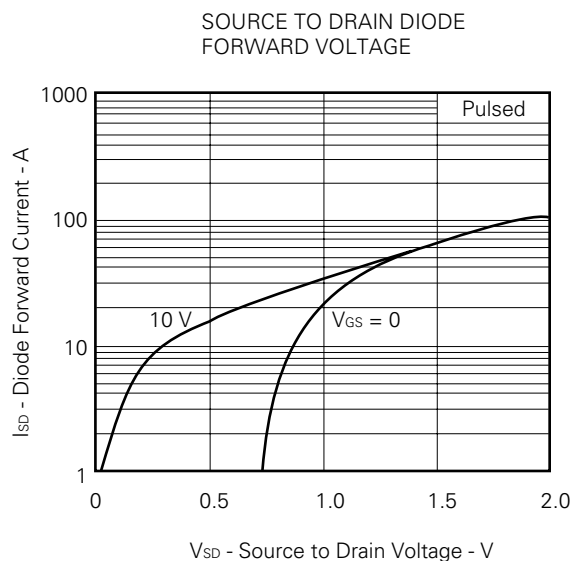
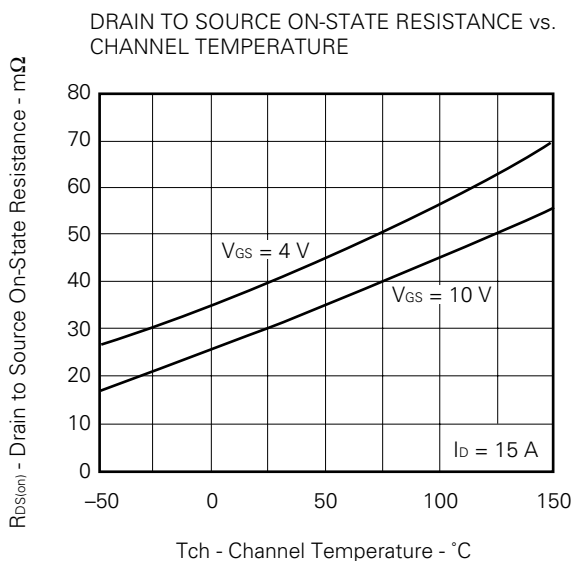


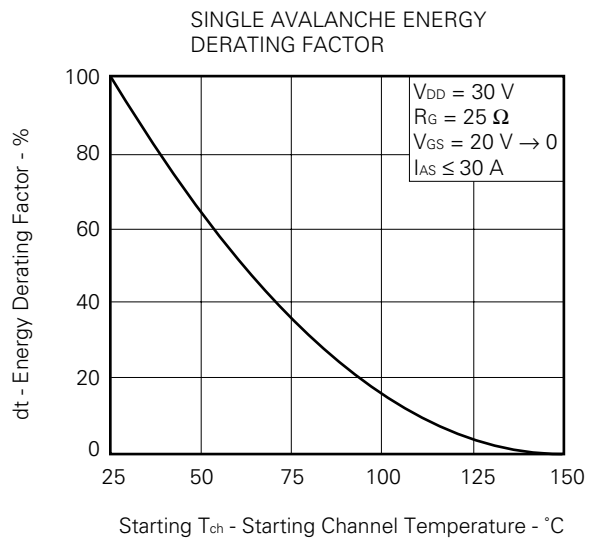
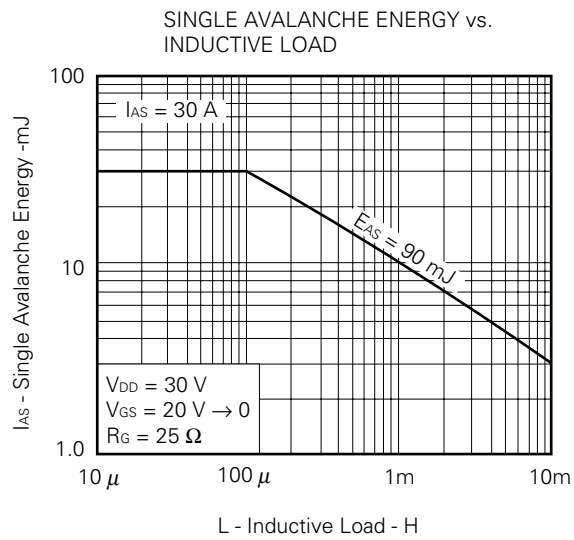
DRAIN TO SOURCE ON-STATE RESISTANCE vs. DRAIN CURRENT



GATE TO SOURCE CUTOFF VOLTAGE vs. CHANNEL TEMPERATURE







REFERENCE

Document Name	Document No.
NEC semiconductor device reliability/quality control system.	TEI-1202
Quality grade on NEC semiconductor devices.	IEI-1209
Semiconductor device mounting technology manual.	IEI-1207
Semiconductor device package manual.	IEI-1213
Guide to quality assurance for semiconductor devices.	MEI-1202
Semiconductor selection guide.	MF-1134
Power MOS FET features and application switching power supply.	TEA-1034
Application circuits using Power MOS FET.	TEA-1035
Safe operating area of Power MOS FET.	TEA-1037

The diode connected between the gate and source of the transistor serves as a protector against ESD. When this device is actually used, an additional protection circuit is externally required if a voltage exceeding the rated voltage may be applied to this device.

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Special: Automotive and Transportation equipment, Traffic control systems, Antidisaster systems, Anticrime systems, etc.